

Silicon PIN Photodiode



21591

DESCRIPTION

T1110P6 is a high speed and high sensitive PIN photodiode chip with 7.5 mm² sensitive area detecting visible and near infrared radiation. Anode is the bond pad on top.

GENERAL INFORMATION

The datasheet is based on Vishay optoelectronics sample testing under certain predetermined and assumed conditions, and is provided for illustration purpose only. Customers are encouraged to perform testing in actual proposed packaged and used conditions. Vishay optoelectronics die products are tested using Vishay optoelectronics based quality assurance procedures and are manufactured using Vishay optoelectronics established processes. Estimates such as those described and set forth in this datasheet for semiconductor die will vary depending on a number of packaging, handling, use, and other factors. Therefore sold die may not perform on an equivalent basis to standard package products.

PRODUCT SUMMARY

COMPONENT	I _{ra} (μA)	φ (deg)	λ _{0.1} (nm)
T1110P6	55	± 60	430 to 1100

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
T1110P6-SD-F	Wafer sawn on foil with disco frame	MOQ: 5000 pcs	Chip

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg1}	- 40 to + 100	°C
Storage temperature range on foil		T _{stg2}	- 40 to + 50	°C

Note

T_{amb} = 25 °C, unless otherwise specified

FEATURES

- Package type: chip
- Package form: single chip
- Dimensions (L x W x H in mm): 2.97 x 2.97 x 0.28
- Radiant sensitive area (in mm²): 7.5
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: φ = ± 60°
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- High speed photo detector

BASIC CHARACTERISTICS ⁽¹⁾						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 100 \mu A, E = 0$	$V_{(BR)}$		60		V
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1	1.3	V
Reverse dark current	$V_R = 10 \text{ V}, E = 0$	I_{ro}		2	5	nA
Diode capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_D		70		pF
	$V_R = 3 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_D		25		pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	V_{OC}		350		mV
Temperature coefficient of V_{OC}	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{VOC}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I_k		50		μA
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$	I_{ra}		55		μA
Angle of half sensitivity		ϕ		± 60		deg
Wavelength of peak sensitivity		λ_p		940		nm
Range of spectral bandwidth		$\lambda_{0.1}$		430 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4×10^{-14}		W/\sqrt{Hz}
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_f		100		ns

Notes(1) $T_{amb} = 25^\circ C$, unless otherwise specified

(2) The measurements are based on samples of die which are mounted on a TO-header without resin coating

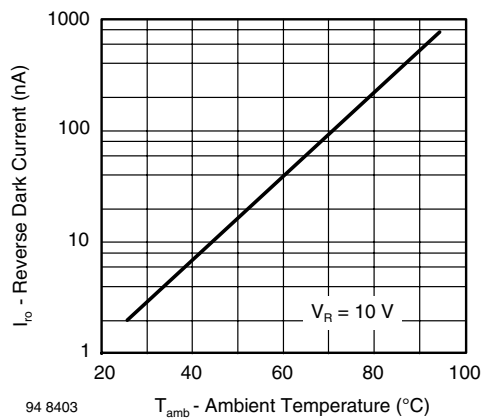
BASIC CHARACTERISTICS $T_{amb} = 25^\circ C$, unless otherwise specified

Fig. 1 - Reverse Dark Current vs. Ambient Temperature

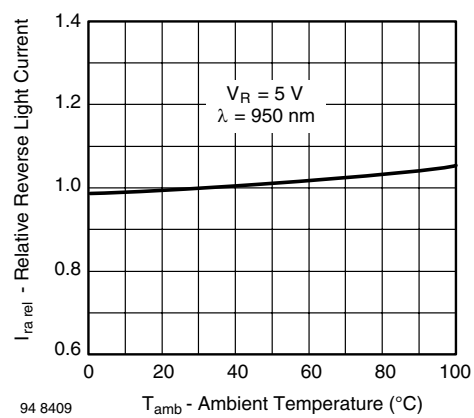


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

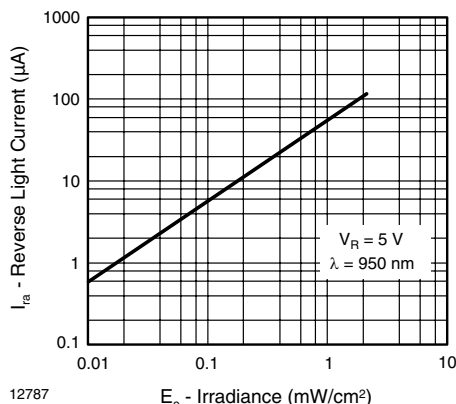


Fig. 3 - Reverse Light Current vs. Irradiance

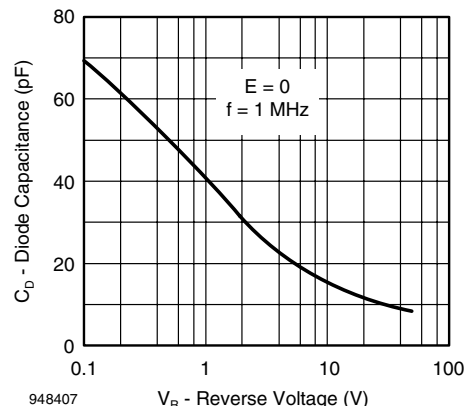


Fig. 5 - Diode Capacitance vs. Reverse Voltage

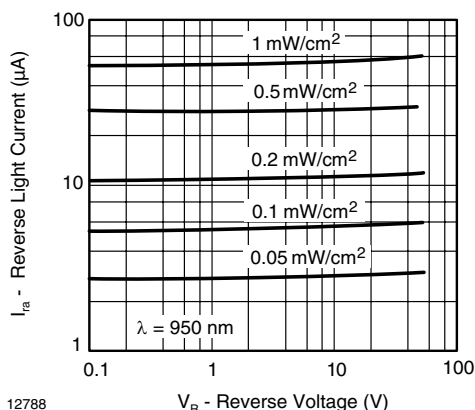


Fig. 4 - Reverse Light Current vs. Reverse Voltage

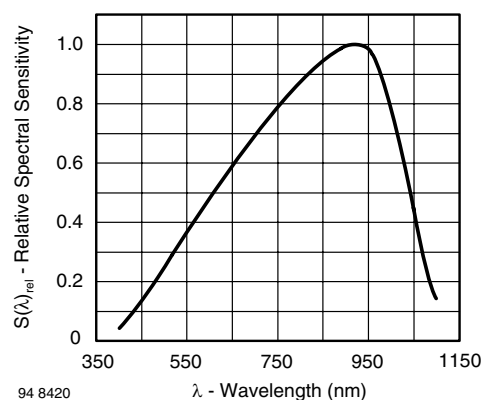


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

MECHANICAL DIMENSIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Length of chip edge (x-direction)	L_x		2.97		mm
Length of chip edge (y-direction)	L_y		2.97		mm
Sensitive area	A_S		2.74 x 2.74		mm ²
Die height	H		0.28		mm
Bond pad anode	a x b		0.2 x 0.2		mm ²

ADDITIONAL INFORMATION (1)

Frontside metallization, anode	Aluminum
Backside metallization, cathode	NiV-Ag
Dicing	Sawing
Die bonding technology	Epoxy bonding

Note

- (1) All chips are checked in accordance with the Vishay Semiconductor, specification of visual inspection FVOV6870. The visual inspection shall be made in accordance with the “specification of visual inspection as referenced”. The visual inspection of chip backside is performed with stereo microscope with incident light and 40x to 80x magnification. The quality inspection (final visual inspection) is performed by production. An additional visual inspection step as special release procedure by QM is not installed.



HANDLING AND STORAGE CONDITIONS

- The hermetically sealed shipment lots shall be opened in temperature and moisture controlled cleanroom environment only. It is mandatory to follow the rules for disposition of material that can be hazardous for humans and environment.
- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Singulated die are not to be handled with tweezers. A vacuum wand with non metallic ESD protected tip should be used.

PACKING

Chips are fixed on adhesive foil. Upon request the foils can be mounted on plastic frame or disco frame. For shipment, the wafers are arranged to stacks and hermetically sealed in plastic bags to ensure protection against environmental influence (humidity and contamination).

Use for recycling reliable operators only. We can help getting in touch with your nearest sales office. By agreement we will take back packing material, if it is sorted. You will have to bear the costs of transport. We will invoice you for any costs incurred for packing material that is returned unsorted or which we are not obliged to accept.

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